To all our customers

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The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK2220, 2SK2221

Silicon N-Channel MOS FET

ADE-208-1352 (Z)
1st. Edition
Mar. 2001

Application

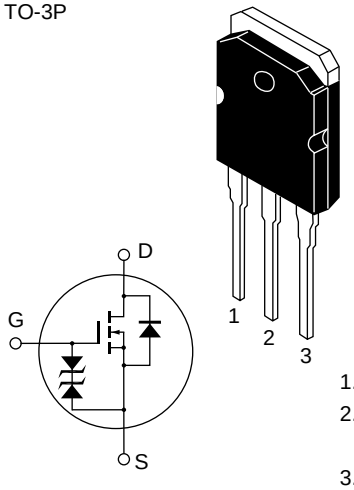
Low frequency power amplifier
Complementary pair with 2SJ351, 2SJ352

Features

- High power gain
- Excellent frequency response
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes

Outline

TO-3P



1. Gate
2. Source
   (Flange)
3. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK2220	V_{DSX}	180	V
	2SK2221		200	
Gate to source voltage		V_{GSS}	±20	V
Drain current		I_D	8	A
Body to drain diode reverse drain current		I_{DR}	8	A
Channel dissipation		Pch*[1]	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

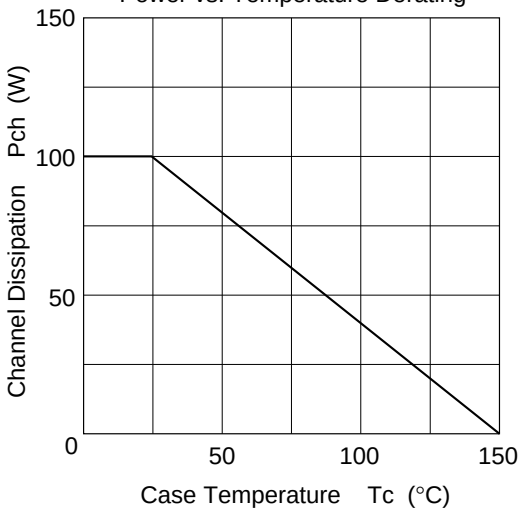
Note 1. Value at Tc = 25 °C

Electrical Characteristics (Ta = 25°C)

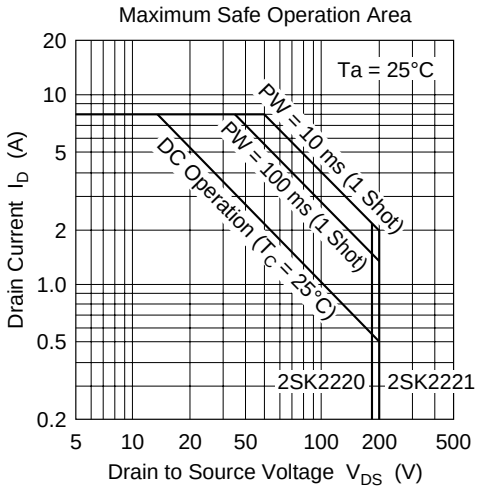
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK2220	$V_{(BR)DSX}$	180	—	—	V	I_D = 10 mA, V_{GS} = –10 V
	2SK2221		200	—	—		
Gate to source breakdown voltage		$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source cutoff voltage		$V_{GS(off)}$	0.15	—	1.45	V	I_D = 100 mA V_{DS} = 10 V
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	12	V	I_D = 8 A, V_{GD} = 0 V*[1]
Forward transfer admittance		$\|y_{fs}\|$	0.7	1.0	1.4	S	I_D = 3 A V_{DS} = 10 V*[1]
Input capacitance		Ciss	—	600	—	pF	V_{GS} = –5 V
Output capacitance		Coss	—	800	—	pF	V_{DS} = 10 V
Reverse transfer capacitance		Crss	—	8	—	pF	f = 1 MHz
Turn-on time		t_{on}	—	250	—	ns	V_{DD} = 30 V
Turn-off time		t_{off}	—	90	—	ns	I_D = 4 A

Note 1. Pulse Test

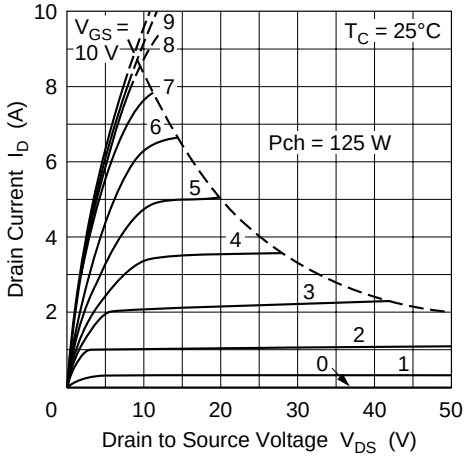
Power vs. Temperature Derating



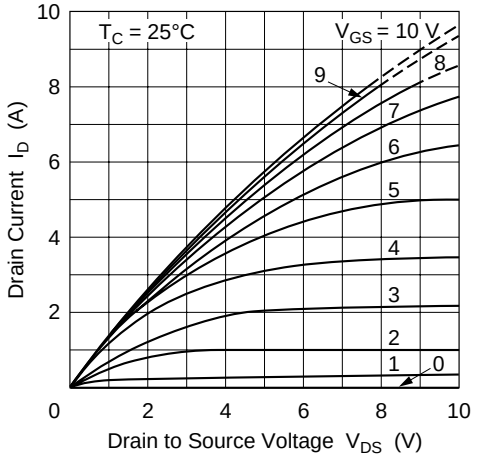
Maximum Safe Operation Area



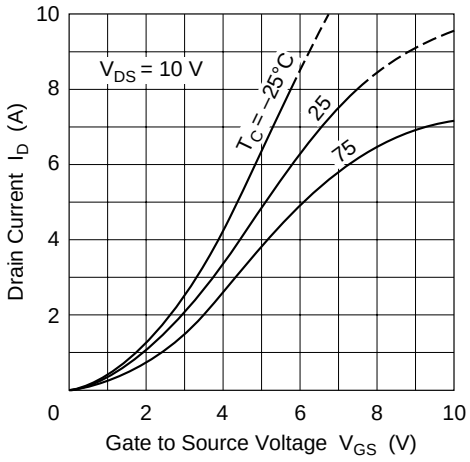
Typical Output Characteristics



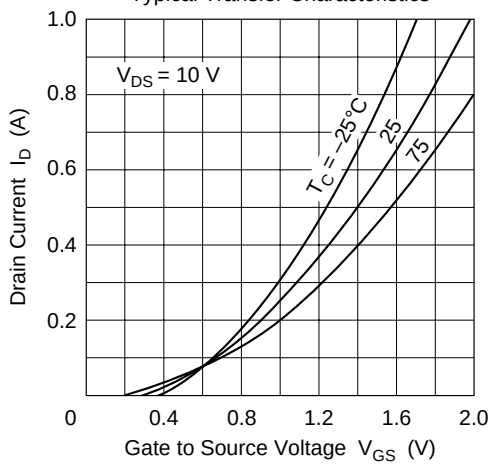
Typical Output Characteristics



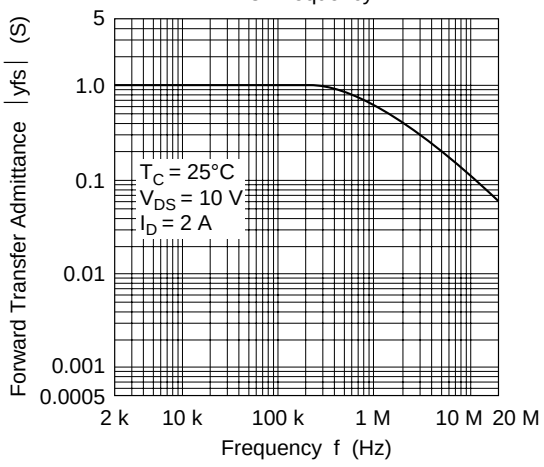
Typical Transfer Characteristics



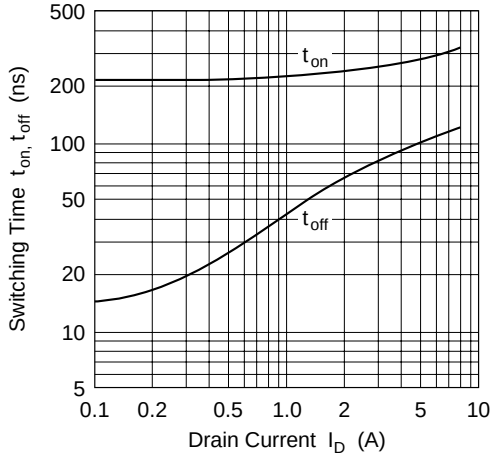
Typical Transfer Characteristics



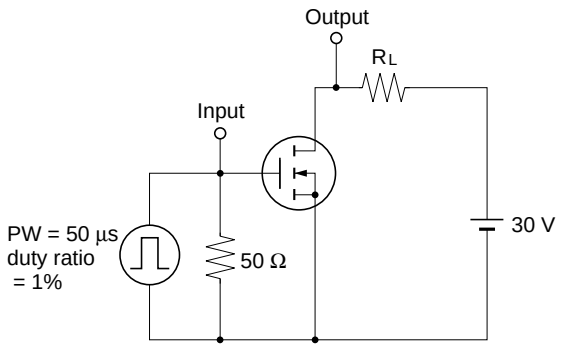
Forward Transfer Admittance vs. Frequency



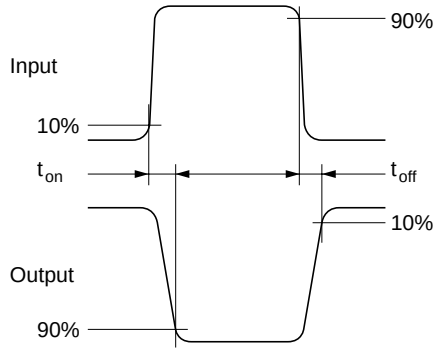
Switching Time vs. Drain Current



Switching Time Test Circuit



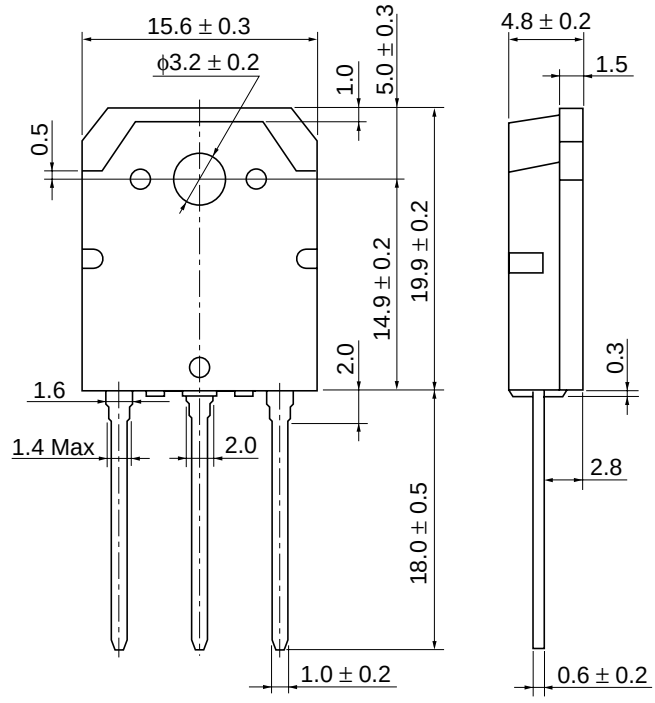
Waveforms

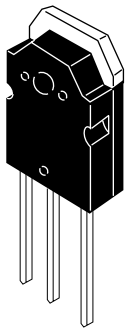


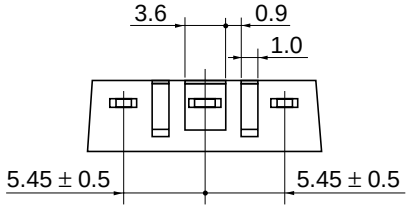
Package Dimensions

As of January, 2001

Unit: mm







Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

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